

UPDATED 08/20/2007

13.75-14.50GHz 2-Watt Internally-Matched Power FET

FEATURES

- 13.75 -14.50GHz Bandwidth
- **Input/Output Impedance Matched to 50 Ohms**
- +33.5 dBm Output Power at 1dB Compression
- 6.5 dB Power Gain at 1dB Compression
- 30% Power Added Efficiency
- -42 dBc IM3 at Po = 22.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}



ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression $f = 13.75-14.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 550\text{mA}$	32.5	33.5		dBm
G _{1dB}	Gain at 1dB Compression $f = 13.75-14.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 550\text{mA}$	5.5	6.5		dB
ΔG	Gain Flatness $f = 13.75-14.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 550\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 550 \text{mA}$ f = 13.75-14.50GHz		30		%
Id_{1dB}	Drain Current at 1dB Compression f = 13.75-14.50GHz		600	700	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 22.5 dBm S.C.L ² V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS f = 14.50GHz	-38	-42		dBc
I _{DSS}	Saturated Drain Current $V_{DS} = 3 \text{ V}, V_{GS} = 0 \text{ V}$		1040	1440	mA
V _P	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 10 \text{ mA}$		-2.5	-4.0	V
R _{TH}	Thermal Resistance ³		11	12	°C/W

Note: 1. Tested with 100 Ohm gate resistor.

2. S.C.L. = Single Carrier Level.

3. Overall Rth depends on case mounting.

ABSOLUTE MAXIMUM RATING FOR EFD

SYMBOLS	PARAMETERS	ABSOLUTE ¹	CONTINUOUS ²	
Vds	Drain-Source Voltage	15V		
Vgs	Gate-Source Voltage	-5V	-4V	
lgf	Forward Gate Current	24mA	7.2mA	
Igr	Reverse Gate Current	-4.8mA	-1.2mA	
Pin	Input Power	33.0dBm	@ 3dB Compression	
Tch	Channel Temperature	175C	175C	
Tstg	Storage Temperature	-65C to +175C	-65C to +175C	
Pt	Total Power Dissipation	12.5W	12.5W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.



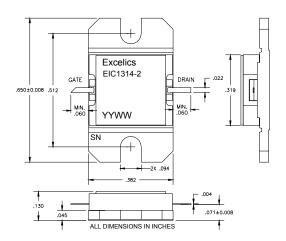
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PACKAGES OUTLINE

Dimensions in inches, Tolerance ± .005 unless otherwise specified

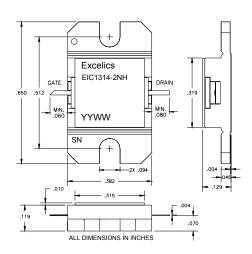
EIC1314-2 (Hermetic)





Caution! ESD sensitive device.

EIC1314-2NH (Non-Hermetic)





Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC1314-2	Hermetic	Industrial	13.75-14.50GHz	32.5	-38
EIC1314-2NH	Non-Hermetic	Industrial	13.75-14.50GHz	32.5	-38

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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